

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a thin film transistor provided between an element to be
5 driven which operates based on supplied power and a power supply
line for supplying power to said element to be driven, for
controlling the power supplied to said element to be driven; wherein

the thin film transistor and corresponding element to be
driven are electrically connected to each other by a wiring layer;
10 and

the contact position between the wiring layer and the thin
film transistor is placed to be distant from the contact position
between the wiring layer and said element to be driven.

15 2. A semiconductor device according to claim 1, wherein

said element to be driven is an emissive element which
includes an emissive element layer between a first electrode and
a second electrode;

a contact hole is formed on an insulation layer which is formed
20 above said wiring layer, said wiring layer being connected through
the contact hole to said first electrode of said emissive element
which is formed on top of said insulation layer and covering said
contact hole;

at least the contact hole region of said first electrode is
25 covered by a flattening layer; and

said emissive element layer is formed above said first
electrode and said flattening layer.

3. A semiconductor device comprising:

a thin film transistor for controlling power supplied to an element to be driven which operates based on the supplied power and which includes an emissive element layer between a first electrode and a second electrode, said thin film transistor provided
5 between said element to be driven and a power supply line for supplying power to said element to be driven; wherein

the thin film transistor and corresponding element to be driven are directly or indirectly and electrically connected to each other at a contact hole formed on an insulation layer for
10 separating said thin film transistor which is formed at a lower layer and said element to be driven;

at least the contact hole region of said first electrode is covered by a flattening layer; and

said emissive element layer is formed above said first
15 electrode and said flattening layer.

4. A semiconductor device according to claim 1, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.